TECHNICAL DATA DATA SHEET 4305, REV -

HERMETIC P-CHANNEL JFET

FEATURES: • 30 V, 75 Ω, 30 mA P-Channel JFET

• Hermetically Sealed

• Surface Mount Package: Ceramic LCC-3

MAXIMUM RATINGS

ALL RATINGS ARE AT $\rm T_A$ = 25°C UNLESS OTHERWISE SPECIFIED.

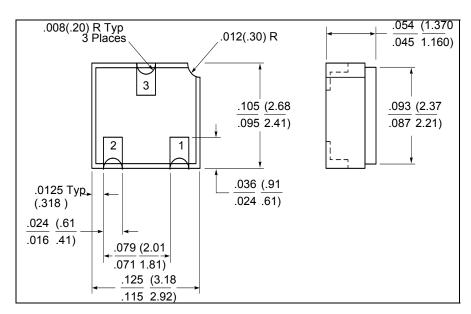
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE $I_D = 1\mu A$, $V_{DS} = 0V$	V_{GS}	-	-	30	V
SATURATED DRAIN CURRENT V _{GS} = 0V, V _{DS} = -18V	I _{DSS}	-30	-	-90	mA
GATE TO DRAIN BREAKDOWN VOLTAGE	BV_GD	-	-	30	V
OPERATING AND STORAGE TEMPERATURE	T _{OP} /T _{STG}	-55	-	+175	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{ heta JC}$	-	-	300	°C/W
TOTAL DEVICE DISSIPATION @ T _C = 25°C	Pn	-	-	0.5	W

ELECTRICAL CHARACTERISTICS

DRAIN TO COURCE ON STATE BESISTANS	\		1	1	1	_
DRAIN TO SOURCE ON STATE RESISTANCE	ΣE	_				Ω
$V_{GS} = 0V$, $I_D = -1$ mA		$R_{DS(ON)}$	-	-	75	
GATE SOURCE CUT OFF VOLTAGE		$V_{GS(OFF)}$	-	5	10	V
$V_{DS} = -15V$, $I_{D} = -1$ nA		,				
COMMON SOURCE TRANSCONDUCTANCE		g fs	-	4.5	-	S(1/Ω)
$V_{DS} = -15V, I_{D} = -1 \text{ mA}$		_				, ,
DRAIN CUT OFF CURRENT,		I _{D(OFF)}	-	- 10	- 500	pА
$V_{DS} = -15V$, $V_{GS} = 12V$ $T_A = 25$ °C		, ,				-
$T_A = 125^{\circ}C$			-	- 0.02	- 1	μΑ
GATE REVERSE CURRENT	V _{GS} = 20V	I _{GSS}	-	5	500	pА
$T_A = 125^{\circ}C$			-	0.01	1	μA
TURN ON DELAY TIME	$V_{DD} = -10V,$	t _{d(ON)}	-	6	-	
RISE TIME I _E	$_{0}$ = - 15 mA,	Ìt _r ´		10		ns
TURN OFF DELAY TIME	$R_G = 100\Omega$,	$t_{d(OFF)}$		6		
FALL TIME	$V_{GS} = 20V$	`t _f		15		
GATE SOURCE FORWARD VOLTAGE	$I_G = -1 \text{ mA}$	$V_{GS(F)}$	-	- 0.7	- 1	V
	$V_{DS} = 0V$	()				
INPUT CAPACITANCE $V_{GS} = 0V, V_{DS} = -15$	V, f = 1MHz	C _{iss}	-	20	25	pF
REVERSE TRANSFER CAPACITANCE		C_{rss}	-	5	7	pF
$V_{GS} = 12V, V_{DS} = 0V, f = 1MHz$		100				'

TECHNICAL DATA DATASHEET 4305, REV. -

MECHANICAL DIMENSIONS - in inches / mm



LCC-3

PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
P Channel JFET	Gate	Source	Drain

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.